

Takashi Suemasu

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#	Paper	IF	Citations
418	Room Temperature 1.6 μm Electroluminescence from a Si-Based Light Emitting Diode with EFeSi_2 Active Region. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, L1013-L1015	1.4	171
417	Optical and electrical properties of semiconducting BaSi_2 thin films on Si substrates grown by molecular beam epitaxy. <i>Thin Solid Films</i> , 2006 , 508, 363-366	2.2	165
416	Epitaxial Growth of Semiconducting BaSi_2 Films on Si(111) Substrates by Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, L478-L481	1.4	125
415	Investigation of the energy band structure of orthorhombic BaSi_2 by optical and electrical measurements and theoretical calculations. <i>Applied Physics Letters</i> , 2002 , 81, 1032-1034	3.4	110
414	Investigation of grain boundaries in BaSi_2 epitaxial films on Si(111) substrates using transmission electron microscopy and electron-beam-induced current technique. <i>Journal of Crystal Growth</i> , 2012 , 348, 75-79	1.6	108
413	Low-temperature (180 $^{\circ}\text{C}$) formation of large-grained Ge (111) thin film on insulator using accelerated metal-induced crystallization. <i>Applied Physics Letters</i> , 2014 , 104, 022106	3.4	88
412	Epitaxial Growth of Semiconducting BaSi_2 Thin Films on Si(111) Substrates by Reactive Deposition Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, 4155-4156	1.4	88
411	Formation of EFeSi_2 Layers on Si(001) Substrates. <i>Japanese Journal of Applied Physics</i> , 1997 , 36, 3620-3624	4.4	84
410	Effect of amorphous Si capping layer on the hole transport properties of BaSi_2 and improved conversion efficiency approaching 10% in p- BaSi_2 /n-Si solar cells. <i>Applied Physics Letters</i> , 2016 , 109, 072103	3.4	82
409	Highly (111)-oriented Ge thin films on insulators formed by Al-induced crystallization. <i>Applied Physics Letters</i> , 2012 , 101, 072106	3.4	78
408	Exploring the possibility of semiconducting BaSi_2 for thin-film solar cell applications. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 07JA01	1.4	76
407	Investigation of the recombination mechanism of excess carriers in undoped BaSi_2 films on silicon. <i>Journal of Applied Physics</i> , 2012 , 112, 083108	2.5	75
406	Influence of Si growth temperature for embedding EFeSi_2 and resultant strain in EFeSi_2 on light emission from p-Si/ EFeSi_2 particles/n-Si light-emitting diodes. <i>Applied Physics Letters</i> , 2001 , 79, 1804-1806	3.4	70
405	Exploring the potential of semiconducting BaSi_2 for thin-film solar cell applications. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 023001	3	69
404	Optical Absorption Properties of BaSi_2 Epitaxial Films Grown on a Transparent Silicon-on-Insulator Substrate Using Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 068001	1.4	65
403	Influence of grain size and surface condition on minority-carrier lifetime in undoped n- BaSi_2 on Si(111). <i>Journal of Applied Physics</i> , 2014 , 115, 193510	2.5	64
402	p- BaSi_2 /n-Si heterojunction solar cells with conversion efficiency reaching 9.0%. <i>Applied Physics Letters</i> , 2016 , 108, 152101	3.4	62

401	In-situ heavily p-type doping of over 10^{20} cm^{-3} in semiconducting BaSi ₂ thin films for solar cells applications. <i>Applied Physics Letters</i> , 2013 , 102, 112107	3.4	59
400	Determination of Bulk Minority-Carrier Lifetime in BaSi ₂ Earth-Abundant Absorber Films by Utilizing a Drastic Enhancement of Carrier Lifetime by Post-Growth Annealing. <i>Applied Physics Express</i> , 2013 , 6, 112302	2.4	58
399	Control of Electron and Hole Concentrations in Semiconducting Silicide BaSi ₂ with Impurities Grown by Molecular Beam Epitaxy. <i>Applied Physics Express</i> , 2008 , 1, 051403	2.4	58
398	Band Diagrams of BaSi ₂ /Si Structure by Kelvin Probe and Current-Voltage Characteristics. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, L519-L521	1.4	58
397	Perpendicular magnetic anisotropy of Mn ₄ N films on MgO(001) and SrTiO ₃ (001) substrates. <i>Journal of Applied Physics</i> , 2014 , 115, 17A935	2.5	57
396	Spin polarization of Fe ₄ N thin films determined by point-contact Andreev reflection. <i>Applied Physics Letters</i> , 2009 , 94, 202502	3.4	57
395	Optical Absorption Edge of Ternary Semiconducting Silicide Ba _{1-x} Sr _x Si ₂ . <i>Japanese Journal of Applied Physics</i> , 2006 , 45, L390-L392	1.4	56
394	Optical Absorption Properties of BaSi ₂ Epitaxial Films Grown on a Transparent Silicon-on-Insulator Substrate Using Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 068001	1.4	56
393	70 °C synthesis of high-Sn content (25%) GeSn on insulator by Sn-induced crystallization of amorphous Ge. <i>Applied Physics Letters</i> , 2015 , 106, 082109	3.4	55
392	Negative differential resistance of metal (CoSi ₂)/insulator (CaF ₂) triple-barrier resonant tunneling diode. <i>Applied Physics Letters</i> , 1993 , 62, 300-302	3.4	54
391	Molecular beam epitaxy of BaSi ₂ thin films on Si(001) substrates. <i>Journal of Crystal Growth</i> , 2012 , 345, 16-21	1.6	53
390	Photoresponse Properties of Polycrystalline BaSi ₂ Films Grown on SiO ₂ Substrates Using (111)-Oriented Si Layers by an Aluminum-Induced Crystallization Method. <i>Applied Physics Express</i> , 2009 , 2, 051601	2.4	52
389	Photoresponse Properties of Semiconducting BaSi ₂ Epitaxial Films Grown on Si(111) Substrates by Molecular Beam Epitaxy. <i>Applied Physics Express</i> , 2009 , 2, 021101	2.4	52
388	Cubic Dominant GaN Growth on (001) GaAs Substrates by Hydride Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1997 , 36, L1-L3	1.4	52
387	High-hole mobility polycrystalline Ge on an insulator formed by controlling precursor atomic density for solid-phase crystallization. <i>Scientific Reports</i> , 2017 , 7, 16981	4.9	51
386	High-Electrical-Conductivity Multilayer Graphene Formed by Layer Exchange with Controlled Thickness and Interlayer. <i>Scientific Reports</i> , 2019 , 9, 4068	4.9	48
385	Aggregation of Monocrystalline FeSi ₂ by Annealing and by Si Overlayer Growth. <i>Japanese Journal of Applied Physics</i> , 1997 , 36, L1225-L1228	1.4	45
384	Orientation Control of Large-Grained Si Films on Insulators by Thickness-Modulated Al-Induced Crystallization. <i>Crystal Growth and Design</i> , 2013 , 13, 1767-1770	3.5	43

383	Direct Growth of [100]-Oriented High-Quality FeSi_2 Films on Si(001) Substrates by Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, L1008-L1011	1.4	43
382	Improved photoresponsivity of semiconducting BaSi_2 epitaxial films grown on a tunnel junction for thin-film solar cells. <i>Applied Physics Letters</i> , 2012 , 100, 152114	3.4	42
381	Impact of Ba to Si deposition rate ratios during molecular beam epitaxy on carrier concentration and spectral response of BaSi_2 epitaxial films. <i>Journal of Applied Physics</i> , 2018 , 123, 045703	2.5	41
380	Analysis of the electrical properties of Cr/n- BaSi_2 Schottky junction and n- BaSi_2 /p-Si heterojunction diodes for solar cell applications. <i>Journal of Applied Physics</i> , 2014 , 115, 223701	2.5	41
379	Fabrication and characterization of polycrystalline BaSi_2 by RF sputtering. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 1759-1761		39
378	Epitaxial growth of semiconducting FeSi_2 and its application to light-emitting diodes. <i>Thin Solid Films</i> , 2004 , 461, 209-218	2.2	39
377	Electrical characterization and conduction mechanism of impurity-doped BaSi_2 films grown on Si(111) by molecular beam epitaxy. <i>Thin Solid Films</i> , 2012 , 522, 95-99	2.2	37
376	Selective formation of large-grained, (100)- or (111)-oriented Si on glass by Al-induced layer exchange. <i>Journal of Applied Physics</i> , 2014 , 115, 094301	2.5	36
375	Molecular beam epitaxy of ferromagnetic Fe_4N thin films on $\text{LaAlO}_3(1\ 0\ 0)$, $\text{SrTiO}_3(1\ 0\ 0)$ and $\text{MgO}(1\ 0\ 0)$ substrates. <i>Journal of Crystal Growth</i> , 2011 , 322, 63-68	1.6	36
374	Control of the Conduction Type of Nondoped High Mobility FeSi_2 Films Grown from Si/Fe Multilayers by Change of Si/Fe Ratios. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, L789-L791	1.4	36
373	Sign of the spin-polarization in cobalt-iron nitride films determined by the anisotropic magnetoresistance effect. <i>Journal of Applied Physics</i> , 2014 , 116, 053912	2.5	35
372	Spin and orbital magnetic moments of molecular beam epitaxy Fe_4N films on $\text{LaAlO}_3(001)$ and $\text{MgO}(001)$ substrates by x-ray magnetic circular dichroism. <i>Applied Physics Letters</i> , 2011 , 98, 102507	3.4	35
371	Growth of SiFeSi_2Bi double-heterostructures on Si(111) substrates by molecular-beam epitaxy and photoluminescence using time-resolved measurements. <i>Journal of Applied Physics</i> , 2004 , 96, 2561-2565	2.5	35
370	Epitaxial Growth of Si-Based Ternary Alloy Semiconductor $\text{Ba}_{1-x}\text{Sr}_x\text{Si}_2$ Films on Si(111) Substrates by Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, L771-L773	1.4	34
369	Influence of air exposure duration and a-Si capping layer thickness on the performance of p- BaSi_2 /n-Si heterojunction solar cells. <i>AIP Advances</i> , 2016 , 6, 085107	1.5	34
368	Operation of BaSi_2 homojunction solar cells on p+-Si(111) substrates and the effect of structure parameters on their performance. <i>Applied Physics Express</i> , 2019 , 12, 041005	2.4	32
367	Realization of single-phase BaSi_2 films by vacuum evaporation with suitable optical properties and carrier lifetime for solar cell applications. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 07JE02	1.4	32
366	Epitaxial growth and magnetic characterization of ferromagnetic Co_4N thin films on $\text{SrTiO}_3(001)$ substrates by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2011 , 336, 40-43	1.6	32

365	Reactive deposition epitaxial growth of FeSi_2 layers on Si(001). <i>Applied Surface Science</i> , 1997 , 117-118, 303-307	6.7	32
364	Metal(CoSi_2)/Insulator(CaF_2) Resonant Tunneling Diode. <i>Japanese Journal of Applied Physics</i> , 1994 , 33, 57-65	1.4	32
363	Epitaxial growth of ferromagnetic Fe_3N films on Si(111) substrates by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2007 , 301-302, 597-601	1.6	31
362	Fabrication and characterization of BaSi_2 epitaxial films over 1 μm in thickness on Si(111). <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 04ER04	1.4	29
361	On the Controlling Mechanism of Preferential Orientation of Polycrystalline-Silicon Thin Films Grown by Aluminum-Induced Crystallization. <i>Applied Physics Express</i> , 2010 , 3, 095803	2.4	29
360	Fabrication of (111)-oriented Si layers on SiO_2 substrates by an aluminum-induced crystallization method and subsequent growth of semiconducting BaSi_2 layers for photovoltaic application. <i>Journal of Crystal Growth</i> , 2009 , 311, 3581-3586	1.6	29
359	Growth of Continuous and Highly (100)-Oriented FeSi_2 Films on Si(001) from Si/Fe Multilayers with SiO_2 Capping and Templates. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, L878-L881	1.4	29
358	Fabrication of n+- BaSi_2 /p+-Si Tunnel Junction on Si(111) Surface by Molecular Beam Epitaxy for Photovoltaic Applications. <i>Applied Physics Express</i> , 2010 , 3, 021301	2.4	28
357	Structural control of organic solar cells based on nonplanar metallophthalocyanine/ C_{60} heterojunctions using organic buffer layers. <i>Organic Electronics</i> , 2011 , 12, 966-973	3.5	28
356	Investigation of direct and indirect band gaps of [100]-oriented nearly strain-free FeSi_2 films grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2002 , 80, 556-558	3.4	28
355	Optimum annealing condition for 1.5 μm photoluminescence from FeSi_2 balls grown by reactive deposition epitaxy and embedded in Si crystal. <i>Journal of Luminescence</i> , 2000 , 87-89, 528-531	3.8	28
354	Improving carrier mobility of polycrystalline Ge by Sn doping. <i>Scientific Reports</i> , 2018 , 8, 14832	4.9	28
353	Structural and electrical characterizations of crack-free BaSi_2 thin films fabricated by thermal evaporation. <i>Thin Solid Films</i> , 2015 , 595, 68-72	2.2	27
352	Precipitation control and activation enhancement in boron-doped p+- BaSi_2 films grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2014 , 104, 252104	3.4	27
351	Growth of Al-doped p-type BaSi_2 films by molecular beam epitaxy and the effect of high-temperature annealing on their electrical properties. <i>Physics Procedia</i> , 2011 , 11, 27-30		27
350	Growth and characterization of group-III impurity-doped semiconducting BaSi_2 films grown by molecular beam epitaxy. <i>Thin Solid Films</i> , 2007 , 515, 8242-8245	2.2	27
349	Growth of Epitaxial FeSi_2 Thin Film on Si(001) by Metal-Organic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, L551-L553	1.4	27
348	Dependence of photoluminescence from FeSi_2 and induced deep levels in Si on the size of FeSi_2 balls embedded in Si crystals. <i>Thin Solid Films</i> , 2001 , 381, 209-213	2.2	27

347	Formation of polycrystalline BaSi ₂ films by radio-frequency magnetron sputtering for thin-film solar cell applications. <i>Thin Solid Films</i> , 2013 , 534, 116-119	2.2	26
346	Improved Surface Quality of the Metal-Induced Crystallized Ge Seed Layer and Its Influence on Subsequent Epitaxy. <i>Crystal Growth and Design</i> , 2015 , 15, 1535-1539	3.5	26
345	Evaluation of potential variations around grain boundaries in BaSi ₂ epitaxial films by Kelvin probe force microscopy. <i>Applied Physics Letters</i> , 2013 , 103, 142113	3.4	26
344	Epitaxial growth and characterization of Si-based light-emitting Si/FeSi ₂ film/Si double heterostructures on Si(001) substrates by molecular beam epitaxy. <i>Thin Solid Films</i> , 2006 , 508, 371-375	2.2	26
343	Photoresponse properties of Al _x -FeSi ₂ Schottky diodes using FeSi ₂ single crystals. <i>Applied Physics Letters</i> , 2007 , 91, 142114	3.4	26
342	Room-temperature electroluminescence of a Si-based p-i-n diode with FeSi ₂ particles embedded in the intrinsic silicon. <i>Journal of Applied Physics</i> , 2005 , 97, 043529	2.5	26
341	Effects of deposition rate on the structure and electron density of evaporated BaSi ₂ films. <i>Journal of Applied Physics</i> , 2016 , 120, 045103	2.5	26
340	Perpendicular magnetic anisotropy in Co _x Mn _{4-x} N (x = 0 and 0.2) epitaxial films and possibility of tetragonal Mn ₄ N phase. <i>AIP Advances</i> , 2016 , 6, 056201	1.5	25
339	p-BaSi ₂ /n-Si heterojunction solar cells on Si(001) with conversion efficiency approaching 10%: comparison with Si(111). <i>Applied Physics Express</i> , 2018 , 11, 062301	2.4	25
338	Large Current Driven Domain Wall Mobility and Gate Tuning of Coercivity in Ferrimagnetic MnN Thin Films. <i>Nano Letters</i> , 2019 , 19, 8716-8723	11.5	25
337	Al- and Cu-doped . <i>Physics Procedia</i> , 2011 , 11, 11-14		25
336	Negative spin polarization at the Fermi level in Fe ₄ N epitaxial films by spin-resolved photoelectron spectroscopy. <i>Journal of Applied Physics</i> , 2012 , 112, 013911	2.5	25
335	Photoluminescence decay time and electroluminescence of p-Si/FeSi ₂ particles/n-Si and p-Si/FeSi ₂ film/n-Si double-heterostructures light-emitting diodes grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2007 , 101, 124506	2.5	25
334	Improvement of the Electrical Properties of FeSi ₂ Films on Si (001) by High-Temperature Annealing. <i>Japanese Journal of Applied Physics</i> , 2000 , 39, L233-L236	1.4	25
333	Direct synthesis of multilayer graphene on an insulator by Ni-induced layer exchange growth of amorphous carbon. <i>Applied Physics Letters</i> , 2017 , 110, 033108	3.4	24
332	Simple way of finding Ba to Si deposition rate ratios for high photoresponsivity in BaSi ₂ films by Raman spectroscopy. <i>Applied Physics Express</i> , 2019 , 12, 055506	2.4	24
331	Fabrication of single-phase polycrystalline BaSi ₂ thin films on silicon substrates by vacuum evaporation for solar cell applications. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 08KC03	1.4	24
330	p-Si/FeSi ₂ /n-Si double-heterostructure light-emitting diodes achieving 1.6 mW electroluminescence of 0.4 mW at room temperature. <i>Applied Physics Letters</i> , 2009 , 94, 213509	3.4	24

329	Optical properties of FeSi_2 under pressure. <i>Physical Review B</i> , 2002 , 65,	3.3	24
328	N-type doping of BaSi_2 epitaxial films by phosphorus ion implantation and thermal annealing. <i>Thin Solid Films</i> , 2014 , 557, 90-93	2.2	23
327	Molecular beam epitaxy of band gap tunable ternary semiconducting silicides $\text{Ba}_{1-x}\text{Sr}_x\text{Si}_2$ for photovoltaic application. <i>Journal of Crystal Growth</i> , 2007 , 301-302, 680-683	1.6	23
326	Fabrication of p-Si/ FeSi_2 /n-Si Double-Heterostructure Light-Emitting Diode by Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 2483-2486	1.4	23
325	Thick and Smooth Hexagonal GaN Growth on GaAs (111) Substrates at 1000°C with Halide Vapor Phase Epitaxy. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, L700-L702	1.4	23
324	Evaluation of band offset at amorphous-Si/ BaSi_2 interfaces by hard x-ray photoelectron spectroscopy. <i>Journal of Applied Physics</i> , 2016 , 119, 165304	2.5	23
323	Metal-induced layer exchange of group IV materials. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 373002	3	22
322	X-ray magnetic circular dichroism of ferromagnetic Co_4N epitaxial films on $\text{SrTiO}_3(001)$ substrates grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2011 , 99, 252501	3.4	22
321	Growth and Characterization of Si-Based Light-Emitting Diode with FeSi_2 -Particles/Si Multilayered Active Region by Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 3951-3953	1.4	22
320	Hole mobility of p-type FeSi_2 thin films grown from Si Fe multilayers. <i>Journal of Applied Physics</i> , 2005 , 97, 093716	2.5	22
319	Improvement of 1.5 μm Photoluminescence from Reactive Deposition Epitaxy (RDE) Grown FeSi_2 Balls in Si by High Temperature Annealing. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, L620-L622	1.4	22
318	Effect of using a high-purity Fe source on the transport properties of p-type FeSi_2 grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , 2007 , 102, 103706	2.5	21
317	Transistor action of metal (CoSi_2)/insulator (CaF_2) hot electron transistor structure. <i>Electronics Letters</i> , 1992 , 28, 1002-1004	1.1	21
316	First-principles study of twin grain boundaries in epitaxial BaSi_2 on Si(111). <i>Journal of Applied Physics</i> , 2016 , 120, 085311	2.5	21
315	Potential variations around grain boundaries in impurity-doped BaSi_2 epitaxial films evaluated by Kelvin probe force microscopy. <i>Journal of Applied Physics</i> , 2014 , 116, 123709	2.5	20
314	N-type doping of BaSi_2 epitaxial films by arsenic ion implantation through a dose-dependent carrier generation mechanism. <i>Thin Solid Films</i> , 2014 , 567, 105-108	2.2	20
313	High-quality multilayer graphene on an insulator formed by diffusion controlled Ni-induced layer exchange. <i>Applied Physics Letters</i> , 2017 , 111, 243104	3.4	20
312	Growth condition dependence of GaN crystal structure on (0 0 1)GaAs by hydride vapor-phase epitaxy. <i>Journal of Crystal Growth</i> , 1998 , 189-190, 395-400	1.6	20

3 ¹¹	High hole mobility ($500 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$) polycrystalline Ge films on GeO ₂ -coated glass and plastic substrates. <i>Applied Physics Express</i> , 2019 , 12, 015508	2.4	20
3 ¹⁰	Control of grain size and crystallinity of poly-Si films on quartz by Al-induced crystallization. <i>CrystEngComm</i> , 2017 , 19, 2305-2311	3.3	19
3 ⁰⁹	Magnetic and magneto-transport properties of Mn ₄ N thin films by Ni substitution and their possibility of magnetic compensation. <i>Journal of Applied Physics</i> , 2019 , 125, 213902	2.5	19
3 ⁰⁸	Vertically Aligned Ge Nanowires on Flexible Plastic Films Synthesized by (111)-Oriented Ge Seeded Vapor-Liquid-Solid Growth. <i>ACS Applied Materials & Interfaces</i> , 2015 , 7, 18120-4	9.5	19
3 ⁰⁷	On the Mechanism of BaSi ₂ Thin Film Formation on Si Substrate by Vacuum Evaporation. <i>Procedia Engineering</i> , 2016 , 141, 23-26		19
3 ⁰⁶	Lattice and grain-boundary diffusions of boron atoms in BaSi ₂ epitaxial films on Si(111). <i>Journal of Applied Physics</i> , 2013 , 113, 053511	2.5	19
3 ⁰⁵	Energetic stability and magnetic moment of tri-, tetra-, and octa-ferromagnetic element nitrides predicted by first-principle calculations. <i>Journal of Alloys and Compounds</i> , 2014 , 611, 440-445	5.7	19
3 ⁰⁴	Dependence of crystal orientation in Al-induced crystallized poly-Si layers on SiO ₂ insertion layer thickness. <i>Journal of Crystal Growth</i> , 2012 , 356, 65-69	1.6	19
3 ⁰³	Fabrication of p-Si/FeSi ₂ balls/n-Si structures by MBE and their electrical and optical properties. <i>Journal of Luminescence</i> , 1998 , 80, 473-477	3.8	19
3 ⁰²	Epitaxial growth of Fe ₃ Si/CaF ₂ /Si(111) hybrid structures by molecular beam epitaxy. <i>Thin Solid Films</i> , 2006 , 508, 78-81	2.2	19
3 ⁰¹	Donor and Acceptor Levels in Undoped FeSi ₂ Films Grown on Si (001) Substrates. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, L249-L251	1.4	19
3 ⁰⁰	Advanced solid-phase crystallization for high-hole mobility ($450 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$) Ge thin film on insulator. <i>Applied Physics Express</i> , 2018 , 11, 031302	2.4	18
2 ⁹⁹	X-ray magnetic circular dichroism for Co _x Fe _{4-x} N (x = 0, 3, 4) films grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2014 , 115, 17C712	2.5	18
2 ⁹⁸	Epitaxial growth and luminescence characterization of Si/FeSi ₂ /Si multilayered structures by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2007 , 301-302, 676-679	1.6	18
2 ⁹⁷	Room temperature negative differential resistance of metal (CoSi ₂)/insulator (CaF ₂) resonant tunnelling diode. <i>Electronics Letters</i> , 1992 , 28, 1432	1.1	18
2 ⁹⁶	Current-Driven Domain Wall Dynamics in Ferrimagnetic Nickel-Doped MnN Films: Very Large Domain Wall Velocities and Reversal of Motion Direction across the Magnetic Compensation Point. <i>Nano Letters</i> , 2021 , 21, 2580-2587	11.5	18
2 ⁹⁵	Negative anisotropic magnetoresistance resulting from minority spin transport in Ni _x Fe _{4-x} N (x = 1 and 3) epitaxial films. <i>Journal of Applied Physics</i> , 2017 , 121, 023903	2.5	17
2 ⁹⁴	Photoresponse properties of BaSi ₂ film grown on Si (100) by vacuum evaporation. <i>Materials Research Express</i> , 2016 , 3, 076204	1.7	17

293	Simple Vacuum Evaporation Route to BaSi ₂ Thin Films for Solar Cell Applications. <i>Procedia Engineering</i> , 2016 , 141, 27-31		17
292	Polycrystalline thin-film transistors fabricated on high-mobility solid-phase-crystallized Ge on glass. <i>Applied Physics Letters</i> , 2019 , 114, 212107	3-4	17
291	Direct synthesis of highly textured Ge on flexible polyimide films by metal-induced crystallization. <i>Applied Physics Letters</i> , 2014 , 104, 262107	3-4	17
290	Orientation control of Ge thin films by underlayer-selected Al-induced crystallization. <i>CrystEngComm</i> , 2014 , 16, 2578	3-3	17
289	Low temperature synthesis of highly oriented p-type Si _{1-x} Ge _x (x: 0.1) on an insulator by Al-induced layer exchange. <i>Journal of Applied Physics</i> , 2017 , 122, 155305	2-5	17
288	Improved Room-Temperature 1.6 μm Electroluminescence from p-Si/FeSi ₂ /n-Si Double Heterostructures Light-Emitting Diodes. <i>Applied Physics Express</i> , 2008 , 1, 021403	2-4	17
287	Measurement of valence-band offset at native oxide/BaSi ₂ interfaces by hard x-ray photoelectron spectroscopy. <i>Journal of Applied Physics</i> , 2016 , 119, 025306	2-5	17
286	Identification of Vibrational Modes in BaSi ₂ Epitaxial Films by Infrared and Raman Spectroscopy. <i>Defect and Diffusion Forum</i> , 2018 , 386, 43-47	0-7	17
285	Thermoelectric Inorganic SiGe Film Synthesized on Flexible Plastic Substrate. <i>ACS Applied Energy Materials</i> , 2018 ,	6-1	17
284	Local electronic states of Fe ₄ N films revealed by x-ray absorption spectroscopy and x-ray magnetic circular dichroism. <i>Journal of Applied Physics</i> , 2015 , 117, 193906	2-5	16
283	Epitaxial growth and magnetic properties of Fe _{4-x} Mn _x N thin films grown on MgO(0 0 1) substrates by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2018 , 489, 20-23	1-6	16
282	Detection of local vibrational modes induced by intrinsic defects in undoped BaSi ₂ light absorber layers using Raman spectroscopy. <i>Journal of Applied Physics</i> , 2018 , 124, 025301	2-5	16
281	Evaluation of minority carrier diffusion length of undoped n-BaSi ₂ epitaxial thin films on Si(001) substrates by electron-beam-induced-current technique. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 078004	1-4	16
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